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Understanding Embedded - FPGAs (Field Programmable Gate Array)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications,

Details

Product Status	Active
Number of LABs/CLBs	-
Number of Logic Elements/Cells	-
Total RAM Bits	18432
Number of I/O	96
Number of Gates	60000
Voltage - Supply	1.425V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 125°C (TA)
Package / Case	144-LBGA
Supplier Device Package	144-FPBGA (13x13)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/a3p060-1fg144t

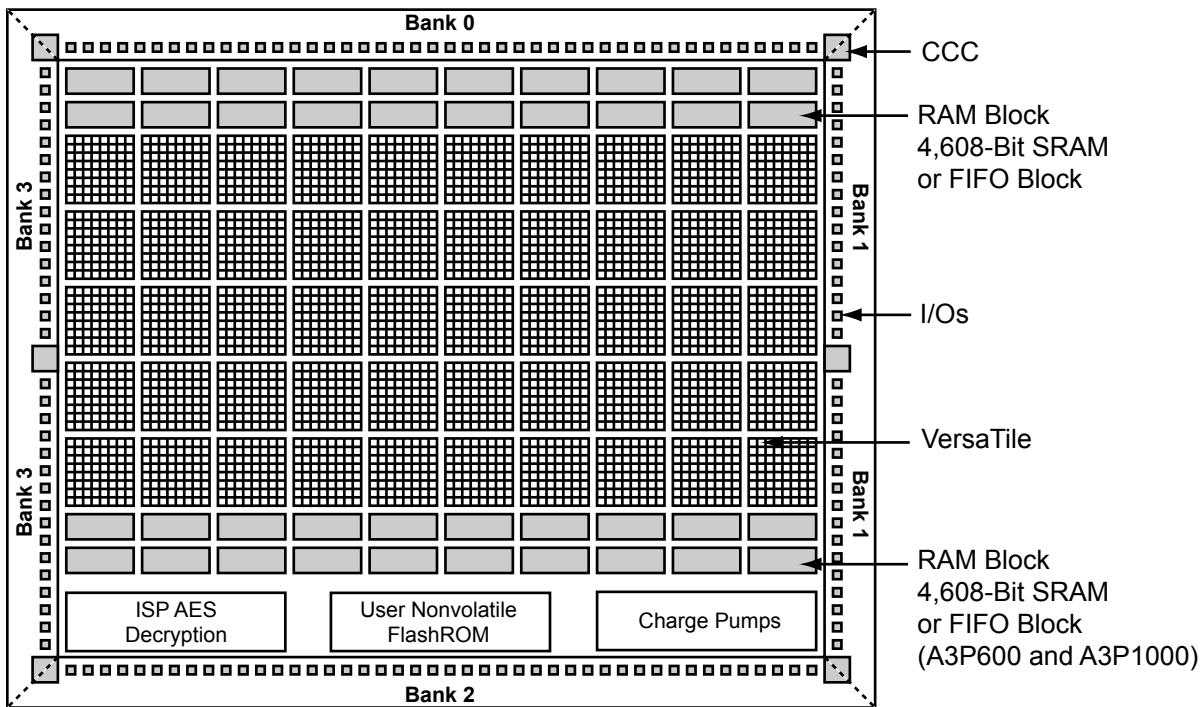


Figure 1-2 • Automotive ProASIC3 Device Architecture Overview with Four I/O Banks (A3P600 and A3P1000)

VersaTiles

The Automotive ProASIC3 core consists of VersaTiles, which have been enhanced beyond the ProASIC^{PLUS®} core tiles. The Automotive ProASIC3 VersaTile supports the following:

- All 3-input logic functions—LUT-3 equivalent
- Latch with clear or set
- D-flip-flop with clear or set
- Enable D-flip-flop with clear or set

Refer to [Figure 1-3](#) for VersaTile configurations.

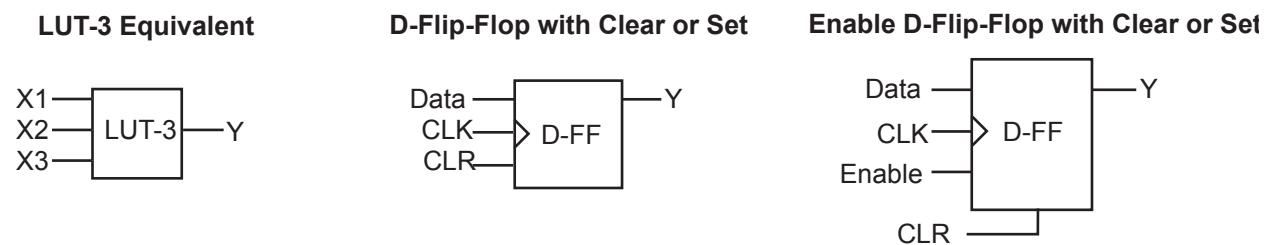


Figure 1-3 • VersaTile Configurations

Calculating Power Dissipation

Quiescent Supply Current

Table 2-6 • Quiescent Supply Current Characteristics

	A3P060	A3P125	A3P250	A3P1000
Typical (25°C)	2 mA	2 mA	3 mA	8 mA
Maximum (Automotive Grade 1) – 135°C	53 mA	53 mA	106 mA	265 mA
Maximum (Automotive Grade 2) – 115°C	26 mA	26 mA	53 mA	131 mA

Note: IDD Includes VCC, VPUMP, VCCI, and VMV currents. Values do not include I/O static contribution, which is shown in [Table 2-7](#) and [Table 2-10](#) on page 2-8.

Power per I/O Pin

Table 2-7 • Summary of I/O Input Buffer Power (per pin) – Default I/O Software Settings¹
Applicable to Advanced I/O Banks

	VMV (V)	Static Power PDC2 (mW) ¹	Dynamic Power PAC9 (μ W/MHz) ²
Single-Ended			
3.3 V LVTTL / 3.3 V LVC MOS	3.3	–	16.69
2.5 V LVC MOS	2.5	–	5.12
1.8 V LVC MOS	1.8	–	2.13
1.5 V LVC MOS (JESD8-11)	1.5	–	1.45
3.3 V PCI	3.3	–	18.11
3.3 V PCI-X	3.3	–	18.11
Differential			
LVDS	2.5	2.26	1.20
LVPECL	3.3	5.72	1.87

Notes:

1. P_{DC2} is the static power (where applicable) measured on VMV.
2. P_{AC9} is the total dynamic power measured on V_{CC} and VMV.

Total Static Power Consumption— P_{STAT}

$$P_{STAT} = PDC1 + N_{INPUTS} * PDC2 + N_{OUTPUTS} * PDC3$$

N_{INPUTS} is the number of I/O input buffers used in the design.

$N_{OUTPUTS}$ is the number of I/O output buffers used in the design.

Total Dynamic Power Consumption— P_{DYN}

$$P_{DYN} = P_{CLOCK} + P_{S-CELL} + P_{C-CELL} + P_{NET} + P_{INPUTS} + P_{OUTPUTS} + P_{MEMORY} + P_{PLL}$$

Global Clock Contribution— P_{CLOCK}

$$P_{CLOCK} = (PAC1 + N_{SPINE} * PAC2 + N_{ROW} * PAC3 + N_{S-CELL} * PAC4) * F_{CLK}$$

N_{SPINE} is the number of global spines used in the user design—guidelines are provided in the "Spine Architecture" section of the Global Resources chapter in the *Automotive ProASIC3 FPGA Fabric User's Guide*.

N_{ROW} is the number of VersaTile rows used in the design—guidelines are provided in the *Automotive ProASIC3 FPGA Fabric User's Guide*.

F_{CLK} is the global clock signal frequency.

N_{S-CELL} is the number of VersaTiles used as sequential modules in the design.

PAC1, PAC2, PAC3, and PAC4 are device-dependent.

Sequential Cells Contribution— P_{S-CELL}

$$P_{S-CELL} = N_{S-CELL} * (PAC5 + \alpha_1 / 2 * PAC6) * F_{CLK}$$

N_{S-CELL} is the number of VersaTiles used as sequential modules in the design. When a multi-tile sequential cell is used, it should be accounted for as 1.

α_1 is the toggle rate of VersaTile outputs—guidelines are provided in [Table 2-12 on page 2-11](#).

F_{CLK} is the global clock signal frequency.

Combinatorial Cells Contribution— P_{C-CELL}

$$P_{C-CELL} = N_{C-CELL} * \alpha_1 / 2 * PAC7 * F_{CLK}$$

N_{C-CELL} is the number of VersaTiles used as combinatorial modules in the design.

α_1 is the toggle rate of VersaTile outputs—guidelines are provided in [Table 2-12 on page 2-11](#).

F_{CLK} is the global clock signal frequency.

Routing Net Contribution— P_{NET}

$$P_{NET} = (N_{S-CELL} + N_{C-CELL}) * \alpha_1 / 2 * PAC8 * F_{CLK}$$

N_{S-CELL} is the number VersaTiles used as sequential modules in the design.

N_{C-CELL} is the number of VersaTiles used as combinatorial modules in the design.

α_1 is the toggle rate of VersaTile outputs—guidelines are provided in [Table 2-12 on page 2-11](#).

F_{CLK} is the global clock signal frequency.

I/O Input Buffer Contribution— P_{INPUTS}

$$P_{INPUTS} = N_{INPUTS} * \alpha_2 / 2 * PAC9 * F_{CLK}$$

N_{INPUTS} is the number of I/O input buffers used in the design.

α_2 is the I/O buffer toggle rate—guidelines are provided in [Table 2-12 on page 2-11](#).

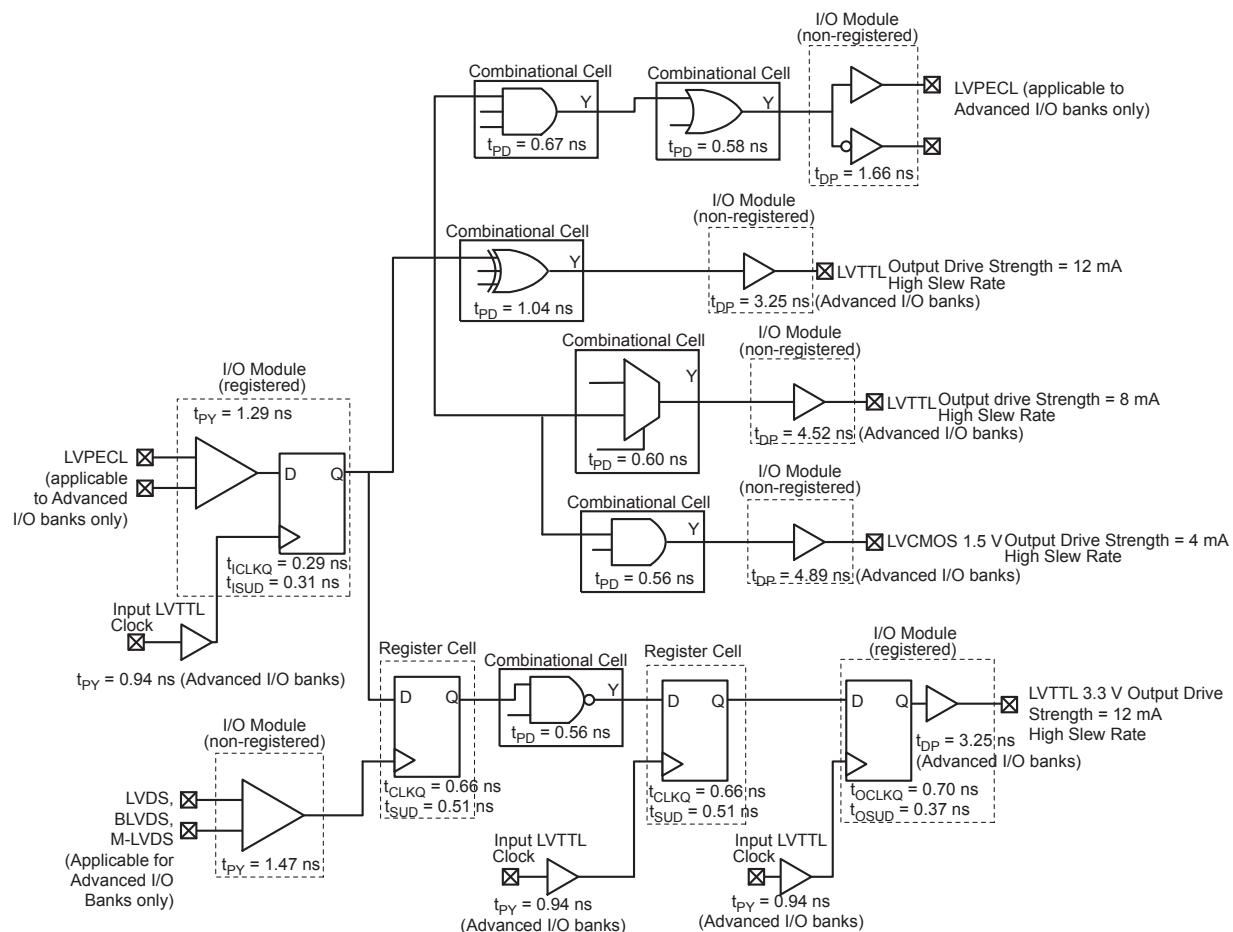
F_{CLK} is the global clock signal frequency.

Table 2-13 • Enable Rate Guidelines Recommended for Power Calculation

Component	Definition	Guideline
β_1	I/O output buffer enable rate	100%
β_2	RAM enable rate for read operations	12.5%
β_3	RAM enable rate for write operations	12.5%

User I/O Characteristics

Timing Model


Figure 2-3 • Timing Model

Operating Conditions: –1 Speed, Automotive Grade 2 Temp. Range ($T_J = 115^\circ\text{C}$), Worst Case
 $VCC = 1.425 \text{ V}$

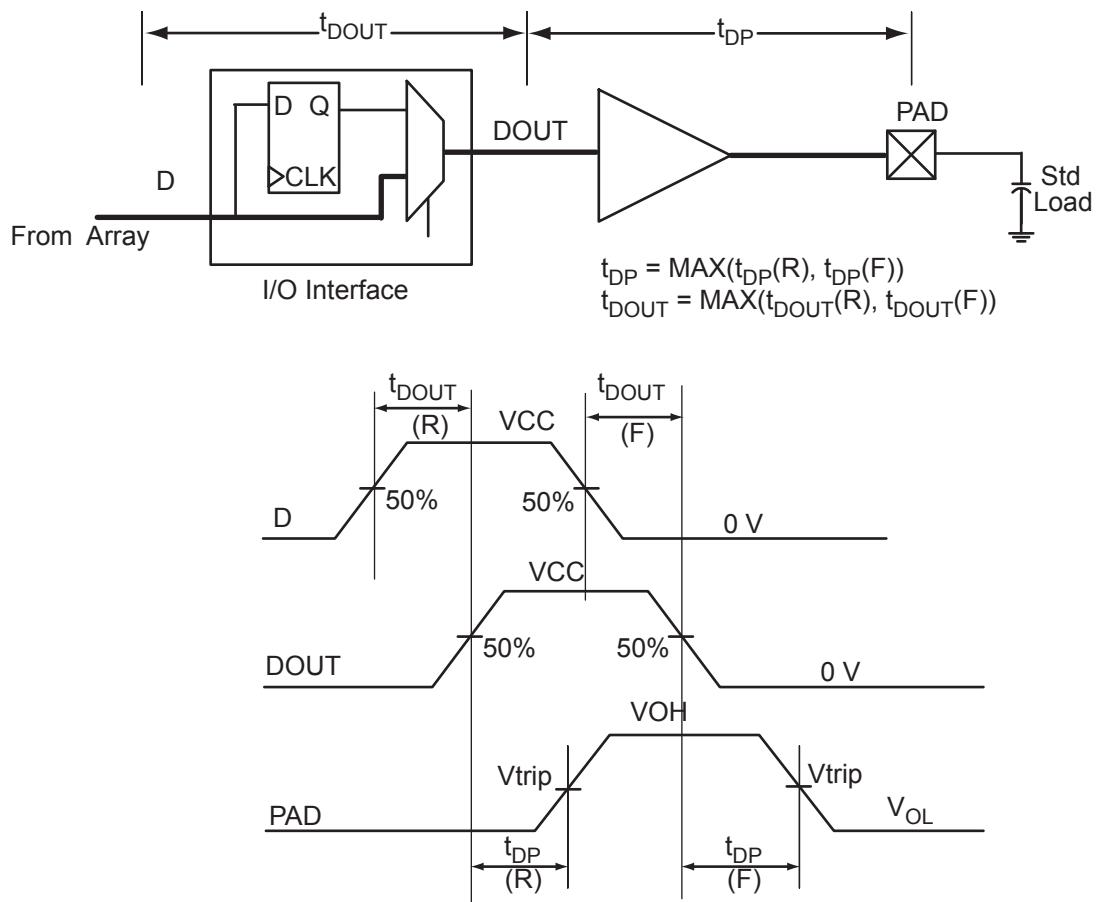


Figure 2-5 • Output Buffer Model and Delays (example)

Table 2-19 • I/O AC Parameter Definitions

Parameter	Parameter Definition
t_{DP}	Data-to-Pad delay through the Output Buffer
t_{PY}	Pad-to-Data delay through the Input Buffer
t_{DOUT}	Data-to-Output Buffer delay through the I/O interface
t_{EOUT}	Enable-to-Output Buffer Tristate Control delay through the I/O interface
t_{DIN}	Input Buffer-to-Data delay through the I/O interface
t_{HZ}	Enable-to-Pad delay through the Output Buffer—High to Z
t_{ZH}	Enable-to-Pad delay through the Output Buffer—Z to High
t_{LZ}	Enable-to-Pad delay through the Output Buffer—Low to Z
t_{ZL}	Enable-to-Pad delay through the Output Buffer—Z to Low
t_{ZHS}	Enable-to-Pad delay through the Output Buffer with delayed enable—Z to High
t_{ZLS}	Enable-to-Pad delay through the Output Buffer with delayed enable—Z to Low

Table 2-20 • Summary of I/O Timing Characteristics—Software Default Settings

–1 Speed Grade, Automotive-Case Conditions: $T_J = 115^\circ\text{C}$, Worst Case VCC = 1.425 V

Worst Case VCCI = 3.0 V

Advanced I/O Banks

I/O Standard	Drive Strength (mA)	Slew Rate	Capacitive Load (pF)	External Resistor (Ω)	t_{DOUT} (ns)	t_{DP} (ns)	t_{DIN} (ns)	t_{PY} (ns)	t_{EOUT} (ns)	t_{ZL} (ns)	t_{ZH} (ns)	t_{LZ} (ns)	t_{HZ} (ns)	t_{ZHS} (ns)	t_{ZLS} (ns)	Units
3.3 V LVTTI / 3.3 V LVCMOS	12 mA	High	35 pF	–	0.53	3.25	0.04	0.94	0.38	3.31	1.51	2.96	1.88	5.37	2.71	ns
2.5 V LVCMOS	12 mA	High	35 pF	–	0.53	3.28	0.04	1.19	0.38	3.34	3.16	1.77	1.80	5.39	5.22	ns
1.8 V LVCMOS	12 mA	High	35 pF	–	0.53	3.25	0.04	1.12	0.38	1.89	1.63	3.41	3.75	3.06	2.82	ns
1.5 V LVCMOS	12 mA	High	35 pF	–	0.53	3.75	0.04	1.32	0.38	2.18	1.91	3.63	3.87	3.35	3.11	ns
3.3 V PCI	Per PCI spec	High	10 pF	25 ²	0.53	2.12	0.04	0.78	0.38	1.23	0.91	2.57	2.96	2.41	2.11	ns
3.3 V PCI-X	Per PCI-X spec	High	10 pF	25 ²	0.53	2.47	0.04	0.77	0.38	1.23	0.91	2.57	2.96	2.41	2.11	ns
LVDS	24 mA	High	–	–	0.53	1.68	0.04	1.47	–	–	–	–	–	–	–	ns
LVPECL	24 mA	High	–	–	0.53	1.66	0.04	1.29	–	–	–	–	–	–	–	ns

Notes:

1. For specific junction temperature and voltage supply levels, refer to [Table 2-5 on page 2-5](#) for derating values.
2. Resistance is used to measure I/O propagation delays as defined in PCI specifications. See [Figure 2-11 on page 2-48](#) for connectivity. This resistor is not required during normal operation.

Table 2-58 • 1.8 V LVC MOS Low Slew

**Automotive-Case Conditions: $T_J = 135^\circ\text{C}$, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 2.3 V
Applicable to Advanced I/O Banks**

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	STD	0.64	17.36	0.05	1.45	0.46	15.78	17.36	1.53	0.87	18.28	19.864	ns
	-1	0.55	14.77	0.04	1.23	0.39	13.42	14.77	1.54	0.87	15.55	16.897	ns
4 mA	STD	0.64	11.71	0.05	1.45	0.46	11.64	11.71	1.78	1.48	14.14	14.214	ns
	-1	0.55	9.96	0.04	1.23	0.39	9.90	9.96	1.78	1.48	12.03	12.091	ns
6 mA	STD	0.64	9.00	0.05	1.45	0.46	9.17	8.77	1.95	1.77	11.67	11.267	ns
	-1	0.55	7.66	0.04	1.23	0.39	7.80	7.46	1.95	1.77	9.92	9.585	ns
8 mA	STD	0.64	8.39	0.05	1.45	0.46	8.54	8.16	1.99	1.85	11.04	10.66	ns
	-1	0.55	7.14	0.04	1.23	0.39	7.27	6.94	1.99	1.85	9.40	9.068	ns
12 mA	STD	0.64	8.15	0.05	1.45	0.46	8.09	8.15	2.05	2.14	10.59	10.654	ns
	-1	0.55	6.94	0.04	1.23	0.39	6.88	6.94	2.05	2.14	9.01	9.063	ns
16 mA	STD	0.64	8.15	0.05	1.45	0.46	8.09	8.15	2.05	2.14	10.59	10.654	ns
	-1	0.55	6.94	0.04	1.23	0.39	6.88	6.94	2.05	2.14	9.01	9.063	ns

Note: For specific junction temperature and voltage supply levels, refer to [Table 2-5 on page 2-5](#) for derating values.

Table 2-59 • 1.8 V LVC MOS High Slew

**Automotive-Case Conditions: $T_J = 135^\circ\text{C}$, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 2.3 V
Applicable to Standard Plus I/O Banks**

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	STD	0.64	13.26	0.05	1.36	0.46	9.75	12.67	1.24	0.82	12.26	15.17	ns
	-1	0.55	11.28	0.04	1.16	0.39	8.30	10.78	1.24	0.83	10.43	12.905	ns
4 mA	STD	0.64	7.73	0.05	1.36	0.46	6.13	7.25	1.46	1.41	8.63	9.749	ns
	-1	0.55	6.58	0.04	1.16	0.39	5.21	6.17	1.46	1.41	7.34	8.293	ns
6 mA	STD	0.64	4.97	0.05	1.36	0.46	4.29	4.54	1.62	1.68	6.79	7.039	ns
	-1	0.55	4.23	0.04	1.16	0.39	3.65	3.86	1.62	1.68	5.78	5.987	ns
8 mA	STD	0.64	4.39	0.05	1.36	0.46	4.29	4.54	1.62	1.68	6.79	7.039	ns
	-1	0.55	3.73	0.04	1.16	0.39	3.65	3.86	1.62	1.68	5.78	5.987	ns

Notes:

1. Software default selection highlighted in gray.
2. For specific junction temperature and voltage supply levels, refer to [Table 2-5 on page 2-5](#) for derating values.

Table 2-70 • 1.5 V LVC MOS High Slew

**Automotive-Case Conditions: $T_J = 135^\circ\text{C}$, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 2.3 V
Applicable to Standard Plus I/O Banks**

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	STD	0.64	8.76	0.05	1.59	0.46	7.63	9.35	1.87	1.50	10.13	11.851	ns
	-1	0.55	7.45	0.04	1.35	0.39	6.49	7.95	1.87	1.50	8.62	10.081	ns
4 mA	STD	0.64	5.41	0.05	1.59	0.46	5.42	5.94	2.07	1.84	7.92	8.442	ns
	-1	0.55	4.60	0.04	1.35	0.39	4.61	5.05	2.07	1.85	6.74	7.181	ns

Notes:

1. Software default selection highlighted in gray.
2. For specific junction temperature and voltage supply levels, refer to [Table 2-5 on page 2-5](#) for derating values.

Table 2-71 • 1.5 V LVC MOS Low Slew

**Automotive-Case Conditions: $T_J = 135^\circ\text{C}$, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 2.3 V
Applicable to Standard Plus I/O Banks**

Drive Strength	Speed Grade	t_{POUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	STD	0.64	13.51	0.05	1.45	0.46	14.32	14.29	1.88	1.43	16.82	16.794	ns
	-1	0.55	11.49	0.04	1.23	0.39	12.18	12.16	1.88	1.43	14.31	14.286	ns
4 mA	STD	0.64	10.38	0.05	1.45	0.46	11.40	10.67	2.07	1.77	13.90	13.175	ns
	-1	0.55	8.83	0.04	1.23	0.39	9.70	9.08	2.07	1.77	11.82	11.207	ns

Note: For specific junction temperature and voltage supply levels, refer to [Table 2-5 on page 2-5](#) for derating values.

Table 2-72 • 1.5 V LVC MOS High Slew

**Automotive-Case Conditions: $T_J = 115^\circ\text{C}$, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 2.3 V
Applicable to Advanced I/O Banks**

Drive Strength	Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	t_{EOUT}	t_{ZL}	t_{ZH}	t_{LZ}	t_{HZ}	t_{ZLS}	t_{ZHS}	Units
2 mA	STD	0.63	9.05	0.05	1.56	0.45	7.38	9.05	1.81	1.45	9.80	11.47	ns
	-1	0.53	7.70	0.04	1.32	0.38	6.28	7.70	1.81	1.45	8.34	9.75	ns
4 mA	STD	0.63	5.75	0.05	1.56	0.45	5.25	5.75	2.00	1.78	7.67	8.17	ns
	-1	0.53	4.89	0.04	1.32	0.38	4.46	4.89	2.00	1.78	6.52	6.95	ns
6 mA	STD	0.63	5.05	0.05	1.56	0.45	4.92	5.05	2.04	1.87	7.34	7.47	ns
	-1	0.53	4.29	0.04	1.32	0.38	4.19	4.29	2.04	1.87	6.24	6.35	ns
8 mA	STD	0.63	4.41	0.05	1.56	0.45	2.18	1.91	4.27	4.55	3.35	3.11	ns
	-1	0.53	3.75	0.04	1.32	0.38	2.18	1.91	3.63	3.87	3.35	3.11	ns
12 mA	STD	0.63	4.41	0.05	1.56	0.45	2.18	1.91	4.27	4.55	3.35	3.11	ns
	-1	0.53	3.75	0.04	1.32	0.38	2.18	1.91	3.63	3.87	3.35	3.11	ns

Notes:

1. Software default selection highlighted in gray.
2. For specific junction temperature and voltage supply levels, refer to [Table 2-5 on page 2-5](#) for derating values.

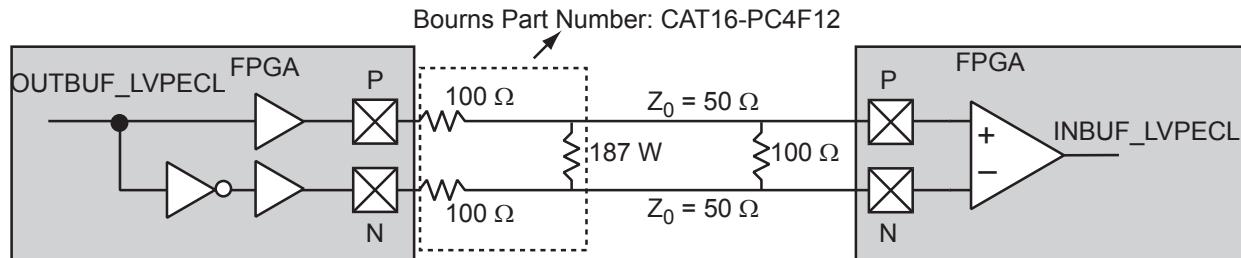


Figure 2-14 • LVPECL Circuit Diagram and Board-Level Implementation

Table 2-86 • Minimum and Maximum DC Input and Output Levels

DC Parameter	Description	Min.	Max.	Min.	Max.	Min.	Max.	Units
VCCI	Supply Voltage	3.0		3.3		3.6		V
VOL	Output Low Voltage	0.96	1.27	1.06	1.43	1.30	1.57	V
VOH	Output High Voltage	1.8	2.11	1.92	2.28	2.13	2.41	V
VIL, VIH	Input Low, Input High Voltages	0	3.6	0	3.6	0	3.6	V
VODIFF	Differential Output Voltage	0.625	0.97	0.625	0.97	0.625	0.97	V
VOCM	Output Common-Mode Voltage	1.762	1.98	1.762	1.98	1.762	1.98	V
VICM	Input Common-Mode Voltage	1.01	2.57	1.01	2.57	1.01	2.57	V
VIDIFF	Input Differential Voltage	300		300		300		mV

Table 2-87 • AC Waveforms, Measuring Points, and Capacitive Loads

Input Low (V)	Input High (V)	Measuring Point* (V)
1.64	1.94	Cross point

Note: *Measuring point = V_{trip} . See [Table 2-18 on page 2-17](#) for a complete table of trip points.

Timing Characteristics

Table 2-88 • LVPECL

Automotive-Case Conditions: $T_J = 135^\circ\text{C}$, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 3.0 V

Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	Units
Std.	0.64	2.01	0.05	1.57	ns
-1	0.55	1.71	0.04	1.34	ns

Note: For specific junction temperature and voltage supply levels, refer to [Table 2-5 on page 2-5](#) for derating values.

Table 2-89 • LVPECL

Automotive-Case Conditions: $T_J = 115^\circ\text{C}$, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 3.0 V

Speed Grade	t_{DOUT}	t_{DP}	t_{DIN}	t_{PY}	Units
Std.	0.63	1.95	0.05	1.52	ns
-1	0.53	1.66	0.04	1.29	ns

Note: For specific junction temperature and voltage supply levels, refer to [Table 2-5 on page 2-5](#) for derating values.

Table 2-97 • Output Enable Register Propagation Delays
Automotive-Case Conditions: $T_J = 115^\circ\text{C}$, Worst-Case VCC = 1.425 V

Parameter	Description	-1	Std.	Units
t_{OECLKQ}	Clock-to-Q of the Output Enable Register	0.53	0.62	ns
t_{OESUD}	Data Setup Time for the Output Enable Register	0.37	0.44	ns
t_{OEHD}	Data Hold Time for the Output Enable Register	0.00	0.00	ns
t_{OESUE}	Enable Setup Time for the Output Enable Register	0.52	0.61	ns
t_{OEHE}	Enable Hold Time for the Output Enable Register	0.00	0.00	ns
$t_{OECLR2Q}$	Asynchronous Clear-to-Q of the Output Enable Register	0.79	0.93	ns
$t_{OEPRE2Q}$	Asynchronous Preset-to-Q of the Output Enable Register	0.79	0.93	ns
$t_{OEREMCLR}$	Asynchronous Clear Removal Time for the Output Enable Register	0.00	0.00	ns
$t_{OERECCR}$	Asynchronous Clear Recovery Time for the Output Enable Register	0.27	0.31	ns
$t_{OEREMPRE}$	Asynchronous Preset Removal Time for the Output Enable Register	0.00	0.00	ns
$t_{OERECPRE}$	Asynchronous Preset Recovery Time for the Output Enable Register	0.27	0.31	ns
t_{OEWCLR}	Asynchronous Clear Minimum Pulse Width for the Output Enable Register	0.25	0.30	ns
t_{OEWPRE}	Asynchronous Preset Minimum Pulse Width for the Output Enable Register	0.25	0.30	ns
$t_{OECKMPWH}$	Clock Minimum Pulse Width High for the Output Enable Register	0.41	0.48	ns
$t_{OECKMPWL}$	Clock Minimum Pulse Width Low for the Output Enable Register	0.37	0.43	ns

Note: For specific junction temperature and voltage supply levels, refer to [Table 2-5 on page 2-5](#) for derating values.

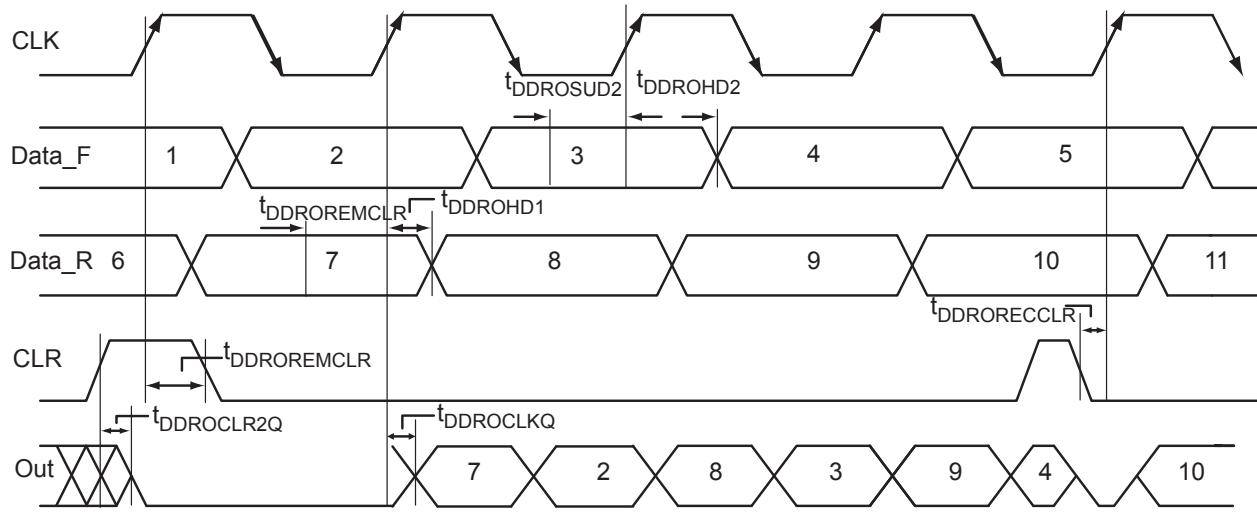


Figure 2-23 • Output DDR Timing Diagram

Timing Characteristics

Table 2-102 • Output DDR Propagation Delays

Commercial-Case Conditions: $T_J = 135^{\circ}\text{C}$, Worst-Case VCC = 1.425 V

Parameter	Description	-1	Std.	Units
$t_{DDROCLKQ}$	Clock-to-Out of DDR for Output DDR	0.85	1.00	ns
$t_{DDROSUD1}$	Data_F Data Setup for Output DDR	0.46	0.54	ns
$t_{DDROSUD2}$	Data_R Data Setup for Output DDR	0.46	0.54	ns
$t_{DDROHD1}$	Data_F Data Hold for Output DDR	0.00	0.00	ns
$t_{DDROHD2}$	Data_R Data Hold for Output DDR	0.00	0.00	ns
$t_{DDROCLR2Q}$	Asynchronous Clear-to-Out for Output DDR	0.97	1.15	ns
$t_{DDROREMCLR}$	Asynchronous Clear Removal Time for Output DDR	0.00	0.00	ns
$t_{DDRORECCLR}$	Asynchronous Clear Recovery Time for Output DDR	0.27	0.32	ns
$t_{DDROWCLR1}$	Asynchronous Clear Minimum Pulse Width for Output DDR	0.25	0.30	ns
$t_{DDROCKMPWH}$	Clock Minimum Pulse Width High for the Output DDR	0.41	0.48	ns
$t_{DDROCKMPWL}$	Clock Minimum Pulse Width Low for the Output DDR	0.37	0.43	ns
F_{DDOMAX}	Maximum Frequency for the Output DDR	309	263	MHz

Note: For specific junction temperature and voltage supply levels, refer to Table 2-5 on page 2-5 for derating values.

Table 2-103 • Output DDR Propagation Delays

 Commercial-Case Conditions: $T_J = 115^\circ\text{C}$, Worst-Case VCC = 1.425 V

Parameter	Description	-1	Std.	Units
$t_{DDROCLKQ}$	Clock-to-Out of DDR for Output DDR	0.84	0.98	ns
$t_{DDROSUD1}$	Data_F Data Setup for Output DDR	0.45	0.53	ns
$t_{DDROSUD2}$	Data_R Data Setup for Output DDR	0.45	0.53	ns
$t_{DDROHD1}$	Data_F Data Hold for Output DDR	0.00	0.00	ns
$t_{DDROHD2}$	Data_R Data Hold for Output DDR	0.00	0.00	ns
$t_{DDROCLR2Q}$	Asynchronous Clear-to-Out for Output DDR	0.96	1.12	ns
$t_{DDOREMCLR}$	Asynchronous Clear Removal Time for Output DDR	0.00	0.00	ns
$t_{DDORECCLR}$	Asynchronous Clear Recovery Time for Output DDR	0.27	0.31	ns
$t_{DDROWCLR1}$	Asynchronous Clear Minimum Pulse Width for Output DDR	0.25	0.30	ns
$t_{DDROCKMPWH}$	Clock Minimum Pulse Width High for the Output DDR	0.41	0.48	ns
$t_{DDROCKMPWL}$	Clock Minimum Pulse Width Low for the Output DDR	0.37	0.43	ns
F_{DDOMAX}	Maximum Frequency for the Output DDR	309	263	MHz

Note: For specific junction temperature and voltage supply levels, refer to Table 2-5 on page 2-5 for derating values.

VersaTile Characteristics

VersaTile Specifications as a Combinatorial Module

The ProASIC3 library offers all combinations of LUT-3 combinatorial functions. In this section, timing characteristics are presented for a sample of the library. For more details, refer to the *Fusion, IGLOO/e, and ProASIC3/E Macro Library Guide*.

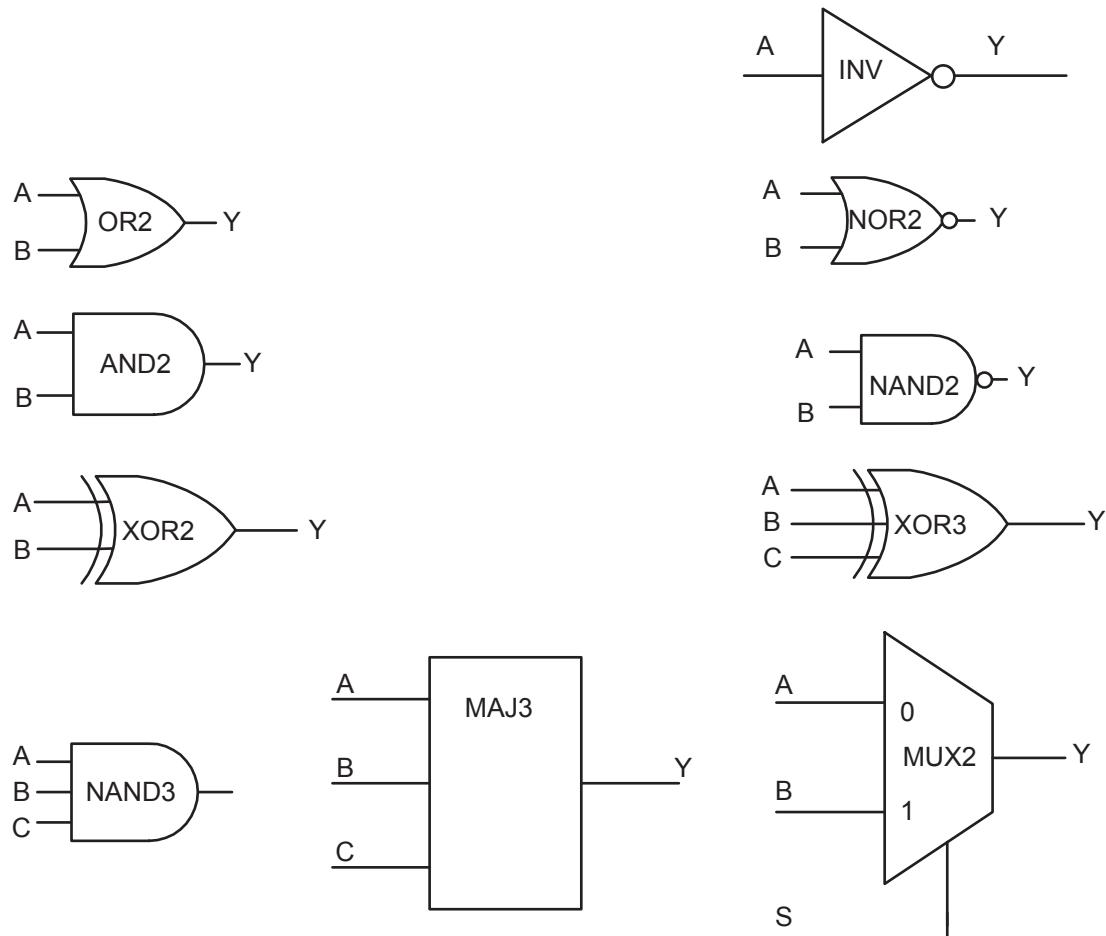


Figure 2-24 • Sample of Combinatorial Cells

Global Tree Timing Characteristics

Global clock delays include the central rib delay, the spine delay, and the row delay. Delays do not include I/O input buffer clock delays, as these are I/O standard-dependent, and the clock may be driven and conditioned internally by the CCC module. For more details on clock conditioning capabilities, refer to the "Clock Conditioning Circuits" section on page 2-80. Table 2-114 on page 2-79 to Table 2-125 on page 2-97 present minimum and maximum global clock delays within each device. Minimum and maximum delays are measured with minimum and maximum loading.

Timing Characteristics

Table 2-108 • A3P060 Global ResourceCommercial-Case Conditions: $T_J = 135^\circ\text{C}$, $VCC = 1.425\text{ V}$

Parameter	Description	-1		Std.		Units
		Min. ¹	Max. ²	Min. ¹	Max. ²	
t_{RCKL}	Input Low Delay for Global Clock	0.87	1.16	1.02	1.37	ns
t_{RCKH}	Input High Delay for Global Clock	0.86	1.20	1.01	1.42	ns
$t_{RCKMPWH}$	Minimum Pulse Width High for Global Clock	0.80		0.94		ns
$t_{RCKMPWL}$	Minimum Pulse Width Low for Global Clock	0.98		1.15		ns
t_{RCKSW}	Maximum Skew for Global Clock		0.35		0.41	ns

Notes:

1. Value reflects minimum load. The delay is measured from the CCC output to the clock pin of a sequential element, located in a lightly loaded row (single element is connected to the global net).
2. Value reflects maximum load. The delay is measured on the clock pin of the farthest sequential element, located in a fully loaded row (all available flip-flops are connected to the global net in the row).
3. For specific junction temperature and voltage supply levels, refer to Table 2-5 on page 2-5 for derating values.

Table 2-109 • A3P060 Global ResourceCommercial-Case Conditions: $T_J = 115^\circ\text{C}$, $VCC = 1.425\text{ V}$

Parameter	Description	-1		Std.		Units
		Min. ¹	Max. ²	Min. ¹	Max. ²	
t_{RCKL}	Input Low Delay for Global Clock	0.85	1.13	1.00	1.33	ns
t_{RCKH}	Input High Delay for Global Clock	0.84	1.18	0.99	1.38	ns
$t_{RCKMPWH}$	Minimum Pulse Width High for Global Clock	0.80		0.94		ns
$t_{RCKMPWL}$	Minimum Pulse Width Low for Global Clock	0.98		1.15		ns
t_{RCKSW}	Maximum Skew for Global Clock		0.34		0.40	ns

Notes:

1. Value reflects minimum load. The delay is measured from the CCC output to the clock pin of a sequential element, located in a lightly loaded row (single element is connected to the global net).
2. Value reflects maximum load. The delay is measured on the clock pin of the farthest sequential element, located in a fully loaded row (all available flip-flops are connected to the global net in the row).
3. For specific junction temperature and voltage supply levels, refer to Table 2-5 on page 2-5 for derating values.

VQ100	
Pin Number	A3P250 Function
1	GND
2	GAA2/IO118UDB3
3	IO118VDB3
4	GAB2/IO117UDB3
5	IO117VDB3
6	GAC2/IO116UDB3
7	IO116VDB3
8	IO112PSB3
9	GND
10	GFB1/IO109PDB3
11	GFB0/IO109NDB3
12	VCOMPLF
13	GFA0/IO108NPB3
14	VCCPLF
15	GFA1/IO108PPB3
16	GFA2/IO107PSB3
17	VCC
18	VCCIB3
19	GFC2/IO105PSB3
20	GEC1/IO100PDB3
21	GEC0/IO100NDB3
22	GEA1/IO98PDB3
23	GEA0/IO98NDB3
24	VMV3
25	GNDQ
26	GEA2/IO97RSB2
27	GEB2/IO96RSB2
28	GEC2/IO95RSB2
29	IO93RSB2
30	IO92RSB2
31	IO91RSB2
32	IO90RSB2
33	IO88RSB2
34	IO86RSB2

VQ100	
Pin Number	A3P250 Function
35	IO85RSB2
36	IO84RSB2
37	VCC
38	GND
39	VCCIB2
40	IO77RSB2
41	IO74RSB2
42	IO71RSB2
43	GDC2/IO63RSB2
44	GDB2/IO62RSB2
45	GDA2/IO61RSB2
46	GNDQ
47	TCK
48	TDI
49	TMS
50	VMV2
51	GND
52	VPUMP
53	NC
54	TDO
55	TRST
56	VJTAG
57	GDA1/IO60USB1
58	GDC0/IO58VDB1
59	GDC1/IO58UDB1
60	IO52NDB1
61	GCB2/IO52PDB1
62	GCA1/IO50PDB1
63	GCA0/IO50NDB1
64	GCC0/IO48NDB1
65	GCC1/IO48PDB1
66	VCCIB1
67	GND
68	VCC

VQ100	
Pin Number	A3P250 Function
69	IO43NDB1
70	GBC2/IO43PDB1
71	GBB2/IO42PSB1
72	IO41NDB1
73	GBA2/IO41PDB1
74	VMV1
75	GNDQ
76	GBA1/IO40RSB0
77	GBA0/IO39RSB0
78	GBB1/IO38RSB0
79	GBB0/IO37RSB0
80	GBC1/IO36RSB0
81	GBC0/IO35RSB0
82	IO29RSB0
83	IO27RSB0
84	IO25RSB0
85	IO23RSB0
86	IO21RSB0
87	VCCIB0
88	GND
89	VCC
90	IO15RSB0
91	IO13RSB0
92	IO11RSB0
93	GAC1/IO05RSB0
94	GAC0/IO04RSB0
95	GAB1/IO03RSB0
96	GAB0/IO02RSB0
97	GAA1/IO01RSB0
98	GAA0/IO00RSB0
99	GNDQ
100	VMV0

QN132	
Pin Number	A3P250 Function
A1	GAB2/IO117UPB3
A2	IO117VPB3
A3	VCCIB3
A4	GFC1/IO110PDB3
A5	GFB0/IO109NPB3
A6	VCCPLF
A7	GFA1/IO108PPB3
A8	GFC2/IO105PPB3
A9	IO103NDB3
A10	VCC
A11	GEA1/IO98PPB3
A12	GEA0/IO98NPB3
A13	GEC2/IO95RSB2
A14	IO91RSB2
A15	VCC
A16	IO90RSB2
A17	IO87RSB2
A18	IO85RSB2
A19	IO82RSB2
A20	IO76RSB2
A21	IO70RSB2
A22	VCC
A23	GDB2/IO62RSB2
A24	TDI
A25	TRST
A26	GDC1/IO58UDB1
A27	VCC
A28	IO54NDB1
A29	IO52NDB1
A30	GCA2/IO51PPB1
A31	GCA0/IO50NPB1
A32	GCB1/IO49PDB1
A33	IO47NSB1
A34	VCC
A35	IO41NPB1
A36	GBA2/IO41PPB1

QN132	
Pin Number	A3P250 Function
A37	GBB1/IO38RSB0
A38	GBC0/IO35RSB0
A39	VCCIB0
A40	IO28RSB0
A41	IO22RSB0
A42	IO18RSB0
A43	IO14RSB0
A44	IO11RSB0
A45	IO07RSB0
A46	VCC
A47	GAC1/IO05RSB0
A48	GAB0/IO02RSB0
B1	IO118VDB3
B2	GAC2/IO116UDB3
B3	GND
B4	GFC0/IO110NDB3
B5	VCOMPLF
B6	GND
B7	GFB2/IO106PSB3
B8	IO103PDB3
B9	GND
B10	GEB0/IO99NDB3
B11	VMV3
B12	GEB2/IO96RSB2
B13	IO92RSB2
B14	GND
B15	IO89RSB2
B16	IO86RSB2
B17	GND
B18	IO78RSB2
B19	IO72RSB2
B20	GND
B21	GNDQ
B22	TMS
B23	TDO
B24	GDC0/IO58VDB1

QN132	
Pin Number	A3P250 Function
B25	GND
B26	IO54PDB1
B27	GCB2/IO52PDB1
B28	GND
B29	GCB0/IO49NDB1
B30	GCC1/IO48PDB1
B31	GND
B32	GBB2/IO42PDB1
B33	VMV1
B34	GBA0/IO39RSB0
B35	GBC1/IO36RSB0
B36	GND
B37	IO26RSB0
B38	IO21RSB0
B39	GND
B40	IO13RSB0
B41	IO08RSB0
B42	GND
B43	GAC0/IO04RSB0
B44	GNDQ
C1	GAA2/IO118UDB3
C2	IO116VDB3
C3	VCC
C4	GFB1/IO109PPB3
C5	GFA0/IO108NPB3
C6	GFA2/IO107PSB3
C7	IO105NPB3
C8	VCCIB3
C9	GEB1/IO99PDB3
C10	GNDQ
C11	GEA2/IO97RSB2
C12	IO94RSB2
C13	VCCIB2
C14	IO88RSB2
C15	IO84RSB2
C16	IO80RSB2

FG256	
Pin Number	A3P1000 Function
G13	GCC1/IO91PPB1
G14	IO90NPB1
G15	IO88PDB1
G16	IO88NDB1
H1	GFB0/IO208NPB3
H2	GFA0/IO207NDB3
H3	GFB1/IO208PPB3
H4	VCOMPLF
H5	GFC0/IO209NPB3
H6	VCC
H7	GND
H8	GND
H9	GND
H10	GND
H11	VCC
H12	GCC0/IO91NPB1
H13	GCB1/IO92PPB1
H14	GCA0/IO93NPB1
H15	IO96NPB1
H16	GCB0/IO92NPB1
J1	GFA2/IO206PSB3
J2	GFA1/IO207PDB3
J3	VCCPLF
J4	IO205NDB3
J5	GFB2/IO205PDB3
J6	VCC
J7	GND
J8	GND
J9	GND
J10	GND
J11	VCC
J12	GCB2/IO95PPB1
J13	GCA1/IO93PPB1
J14	GCC2/IO96PPB1
J15	IO100PPB1
J16	GCA2/IO94PSB1

FG256	
Pin Number	A3P1000 Function
K1	GFC2/IO204PDB3
K2	IO204NDB3
K3	IO203NDB3
K4	IO203PDB3
K5	VCCIB3
K6	VCC
K7	GND
K8	GND
K9	GND
K10	GND
K11	VCC
K12	VCCIB1
K13	IO95NPB1
K14	IO100NPB1
K15	IO102NDB1
K16	IO102PDB1
L1	IO202NDB3
L2	IO202PDB3
L3	IO196PPB3
L4	IO193PPB3
L5	VCCIB3
L6	GND
L7	VCC
L8	VCC
L9	VCC
L10	VCC
L11	GND
L12	VCCIB1
L13	GDB0/IO112NPB1
L14	IO106NDB1
L15	IO106PDB1
L16	IO107PDB1
M1	IO197NSB3
M2	IO196NPB3
M3	IO193NPB3
M4	GEC0/IO190NPB3

FG256	
Pin Number	A3P1000 Function
M5	VMV3
M6	VCCIB2
M7	VCCIB2
M8	IO147RSB2
M9	IO136RSB2
M10	VCCIB2
M11	VCCIB2
M12	VMV2
M13	IO110NDB1
M14	GDB1/IO112PPB1
M15	GDC1/IO111PDB1
M16	IO107NDB1
N1	IO194PSB3
N2	IO192PPB3
N3	GEC1/IO190PPB3
N4	IO192NPB3
N5	GNDQ
N6	GEA2/IO187RSB2
N7	IO161RSB2
N8	IO155RSB2
N9	IO141RSB2
N10	IO129RSB2
N11	IO124RSB2
N12	GNDQ
N13	IO110PDB1
N14	VJTAG
N15	GDC0/IO111NDB1
N16	GDA1/IO113PDB1
P1	GEB1/IO189PDB3
P2	GEB0/IO189NDB3
P3	VMV2
P4	IO179RSB2
P5	IO171RSB2
P6	IO165RSB2
P7	IO159RSB2
P8	IO151RSB2

FG256	
Pin Number	A3P1000 Function
P9	IO137RSB2
P10	IO134RSB2
P11	IO128RSB2
P12	VMV1
P13	TCK
P14	VPUMP
P15	TRST
P16	GDA0/IO113NDB1
R1	GEA1/IO188PDB3
R2	GEA0/IO188NDB3
R3	IO184RSB2
R4	GEC2/IO185RSB2
R5	IO168RSB2
R6	IO163RSB2
R7	IO157RSB2
R8	IO149RSB2
R9	IO143RSB2
R10	IO138RSB2
R11	IO131RSB2
R12	IO125RSB2
R13	GDB2/IO115RSB2
R14	TDI
R15	GNDQ
R16	TDO
T1	GND
T2	IO183RSB2
T3	GEB2/IO186RSB2
T4	IO172RSB2
T5	IO170RSB2
T6	IO164RSB2
T7	IO158RSB2
T8	IO153RSB2
T9	IO142RSB2
T10	IO135RSB2
T11	IO130RSB2
T12	GDC2/IO116RSB2

FG256	
Pin Number	A3P1000 Function
T13	IO120RSB2
T14	GDA2/IO114RSB2
T15	TMS
T16	GND

Revision	Changes	Page
Revision 2 (continued)	The "Pin Descriptions and Packaging" chapter has been added (SAR 34767),	3-1
	The "VQ100" pin table for A3P125 has been added (SAR 37944).	4-3
	Package names used in the "Package Pin Assignments" section were revised to match standards given in <i>Package Mechanical Drawings</i> (SAR 34767).	4-1
July 2010	The versioning system for datasheets has been changed. Datasheets are assigned a revision number that increments each time the datasheet is revised. The " Automotive ProASIC3 Device Status " table on page II indicates the status for each device in the device family.	N/A

Revision	Changes	Page
Revision 1 (Dec 2009) Product Brief v1.1	The QNG132 package was added to the " Automotive ProASIC3 Product Family " table, " I/Os Per Package " table, " Automotive ProASIC3 Ordering Information ", and " Temperature Grade Offerings ".	I – IV
Packaging v1.1	Pin tables for A3P125 and A3P250 were added for the " QN132 " package.	4-6